





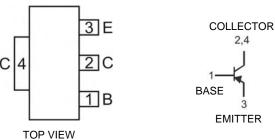
Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZT853)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	Ic	-5	A
Power Dissipation	P _{tot}	1(Note 3) 3(Note 4)	W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.
- 4. The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-140		_	V	$I_C = -100\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100	_	_	V	$I_C = -10 \text{mA*}, I_B = 0$		
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6		_	V	$I_E = -100 \mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}		_	-50 -1	nA μA	$V_{CB} = -100V, I_E = 0$ $V_{CB} = -100V, I_E = 0, T_A = 100^{\circ}C$		
Emitter Cutoff Current	I _{EBO}	_		-10	nA	$V_{EB} = -6V, I_C = 0$		
ON CHARACTERISTICS								
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-20 -90 -160 -300	-50 -115 -220 -420	mV	$\begin{split} I_C &= -100 \text{mA}, \ I_B = -10 \text{mA}^* \\ I_C &= -1\text{A}, \ I_B = -100 \text{mA}^* \\ I_C &= -2\text{A}, \ I_B = -200 \text{mA}^* \\ I_C &= -4\text{A}, \ I_B = -400 \text{mA}^* \end{split}$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1010	-1170	mV	$I_C = -4A, I_B = -400 \text{mA}^*$		
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$		-925	-1160	mV	$I_{CE} = -4A, V_{CE} = -1V^*$		
DC Current Gain	h _{FE}	100 100 50 30		300 — — —	_	$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -1 \text{A}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -3 \text{A}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -4 \text{A}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -10 \text{A}, \ V_{CE} = -1 \text{V}^* \end{split}$		
SMALL SIGNAL CHARACTERISTICS	•							
Current Gain-Bandwidth Product	f _T		125	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz		
Output Capacitance			65	_	pF	$V_{CB} = -10V$, $f = 1MHz$		
SWITCHING CHARACTERISTICS								
Switching Times	t _{on}		110 460	_	ns	I _C = -2A, I _{B1} = -200mA		
Ownerming Times	t _{off}					$I_{B2} = 200 \text{mA}, V_{CC} = -10 \text{V}$		

^{*}Measured under pulsed conditions. Pulse width = 300 μ s. Duty cycle \leq 2%

Typical Characteristics @T_{amb} = 25°C unless otherwise specified

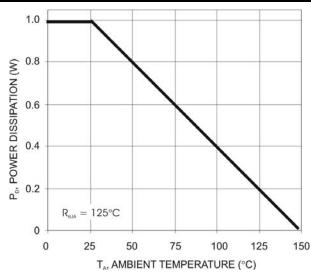


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

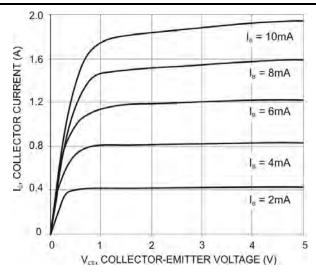


Fig. 2 Collector Current vs. Collector Emitter Voltage

3. Device mounted on FR-4 PCB, pad layout as shown on page 4.



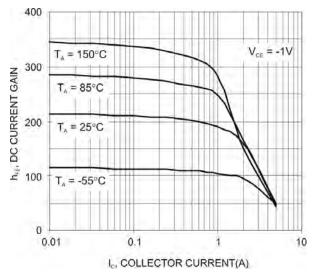


Fig. 3 Typical DC Current Gain vs. Collector Current

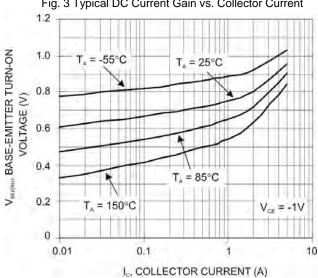


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

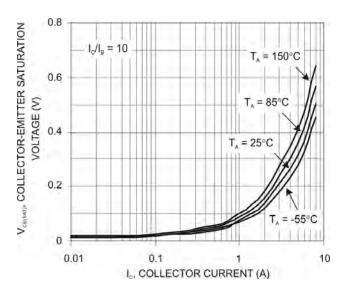


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

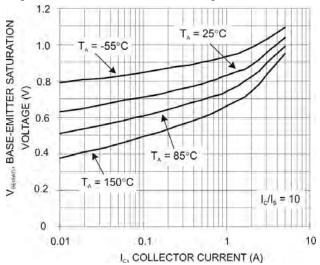


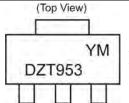
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Valid Marking Codes	Packaging	Shipping
DZT953-13	DZT953	SOT-223	2500/Tape & Reel
DZT953-13	PT06	SOT-223	2500/Tape & Reel

5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

Marking Information



DZT953 or PT06= Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006

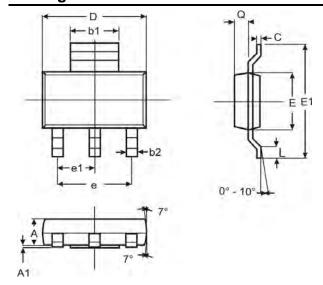
M = Month ex: 9 = September

Date Code Key

Date Code Ney												
Year	200	6	2007		2008	20	09	2010		2011	1	2012
Code	Т		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

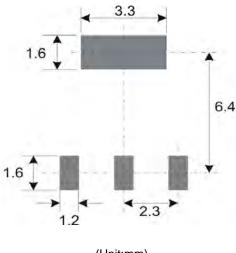


Package Outline Dimensions



SOT-223								
Dim	Min	Max	Тур					
Α	1.55	1.65	1.60					
A 1	0.010	0.15	0.05					
b1	2.90	3.10	3.00					
b2	0.60	0.80	0.70					
С	0.20	0.30	0.25					
D	6.45	6.55	6.50					
Е	3.45	3.55	3.50					
E1	6.90	7.10	7.00					
е	_	1	4.60					
e1	_		2.30					
L	L 0.85		0.95					
Q	0.84	0.94	0.89					
All Dimensions in mm								

Suggested Pad Layout: (Based on IPC-SM-782)



(Unit:mm)

IMPORTANT NOTICE

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